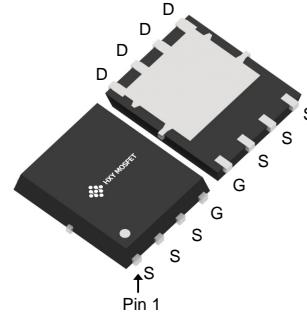




General Description

The TQM075NH10CR use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics. This device is specially designed to get better ruggedness.



DFN5X6-8L

$V_{DS} = 100V$ $I_D = 80A$

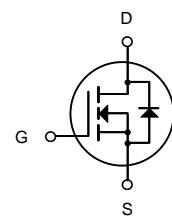
$R_{DS(ON)} < 7m\Omega$ @ $V_{GS}=10V$

Applications

Consumer electronic power supply Motor control

Synchronous-rectification Isolated DC

Synchronous-rectification applications



N-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
TQM075NH10CR	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings at $T_j=25^\circ C$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	100	V
Gate source voltage	V_{GS}	± 20	V
Continuous drain current	I_D	80	A
Pulsed drain current	I_D , pulse	300	A
Power dissipation	P_D	97	W
Single pulsed avalanche energy	E_{AS}	90	mJ
Operation and storage temperature	T_{stg} , T_j	-55 to 150	$^\circ C$
Thermal resistance, junction-case	$R_{\theta JC}$	1.3	$^\circ C/W$



Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristics						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=100\text{V}$, $V_{\text{GS}}=0\text{V}$,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{\text{DS}}=0\text{V}$, $V_{\text{GS}}= \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$, $I_D=250\mu\text{A}$	1.0	1.6	2.5	V
$R_{\text{DS}(\text{on})}$ note3	Static Drain-Source on-Resistance	$V_{\text{GS}}=10\text{V}$, $I_D=20\text{A}$	-	6.4	7	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}$, $I_D=8\text{A}$	-	9.2	11.4	$\text{m}\Omega$
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{\text{DS}}=50\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1.0\text{MHz}$	-	2944	-	pF
C_{oss}	Output Capacitance		-	736	-	pF
C_{rss}	Reverse Transfer Capacitance		-	2.04	-	pF
Q_g	Total Gate Charge		-	39.4	-	nc
Q_{gs}	Gate-Source Charge		-	5.6	-	nc
Q_{gd}	Gate-Drain("Miller") Charge		-	7.6	-	nc
Switching Characteristics						
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$V_{\text{DD}}=50\text{V}$, $I_D=25\text{A}$, $R_G=6\Omega$, $V_{\text{GS}}=10\text{V}$	-	13	-	nc
t_r	Turn-on Rise Time		-	27.5	-	nc
$t_{\text{d}(\text{off})}$	Turn-off Delay Time		-	45.5	-	nc
t_f	Turn-off Fall Time		-	41.5	-	nc
Drain-Source Diode Characteristics and Maximum Ratings						
I_{S}	Maximum Continuous Drain to Source Diode Forward Current	-	-	75	-	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	300	-	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{\text{GS}}=0\text{V}$, $I_{\text{S}}=30\text{A}$	-	-	1	V
t_{rr}	Body Diode Reverse Recovery Time	$T_J=25^\circ\text{C}$, $I_F=12\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$	-	177	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	1291	-	nc

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^\circ\text{C}$, $V_{\text{DD}}=50\text{V}$, $V_G=10\text{V}$, $R_G=25\Omega$, $L=0.5\text{mH}$, $I_{\text{AS}}=19\text{A}$

3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$



Typical Performance Characteristics

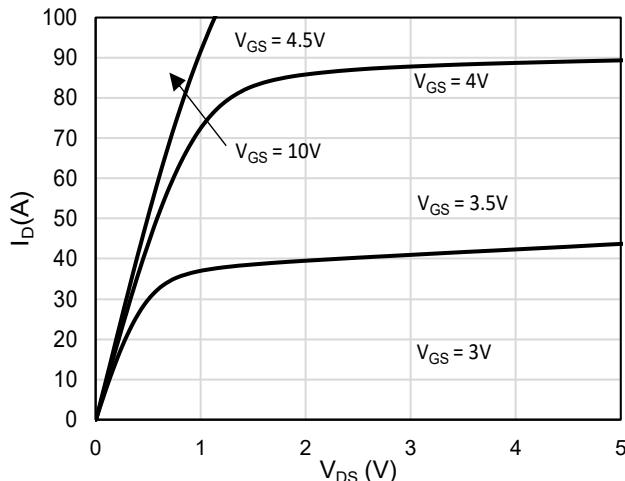


Figure 1: On-Region Characteristics

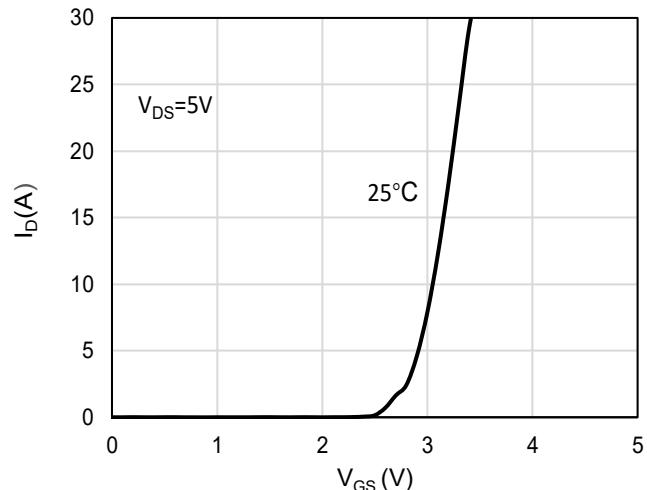


Figure 2: Transfer Characteristics

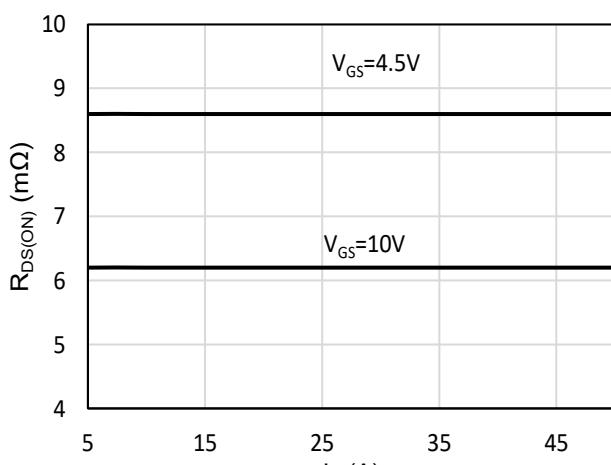


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

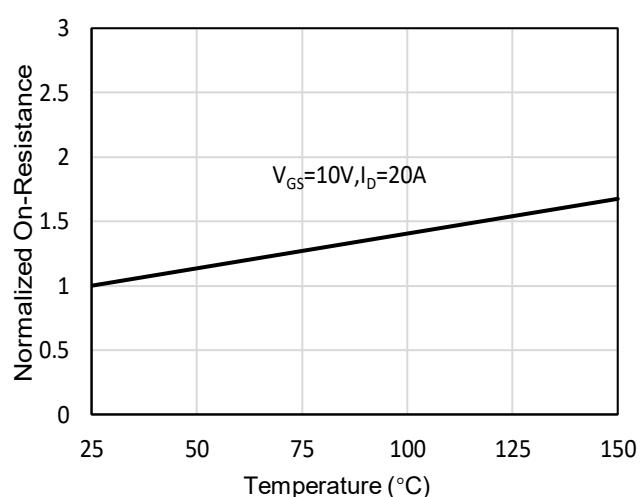


Figure 4: On-Resistance vs. Junction Temperature

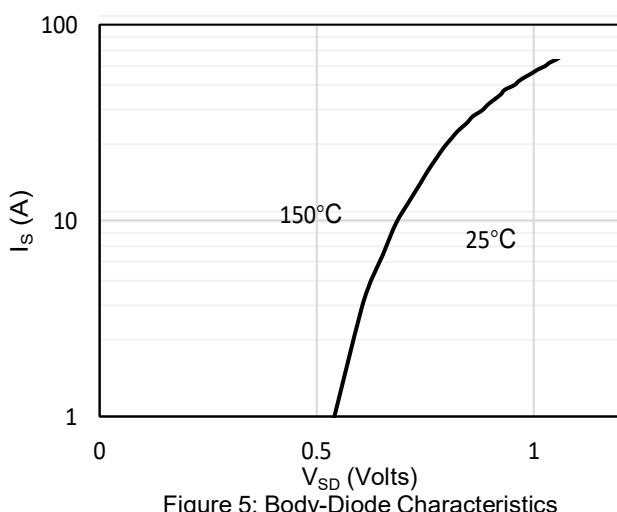


Figure 5: Body-Diode Characteristics

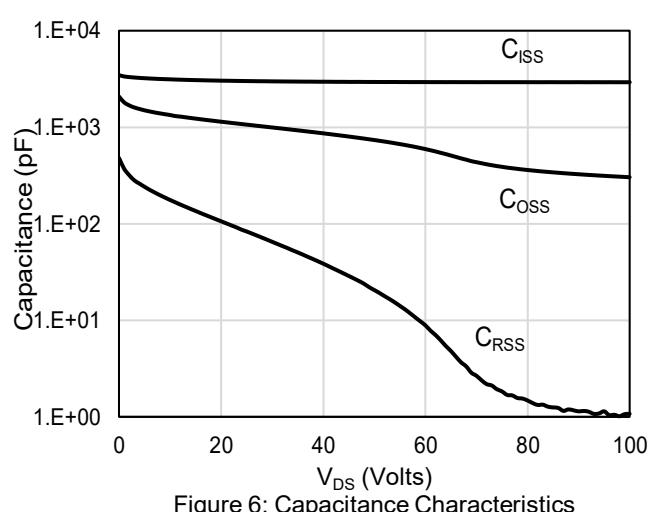


Figure 6: Capacitance Characteristics

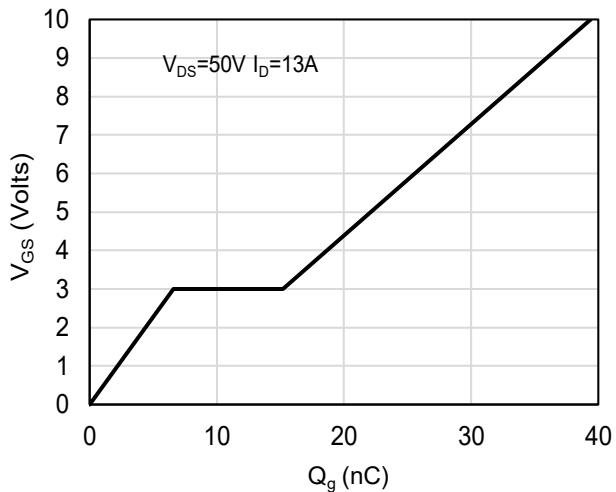


Figure 7: Gate-Charge Characteristics

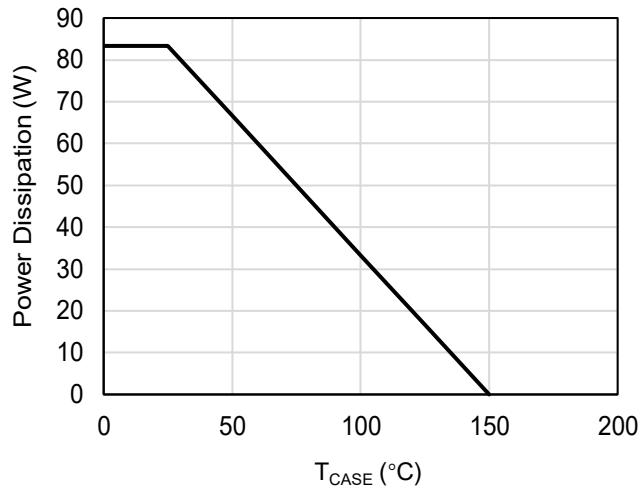


Figure 8: Power De-rating

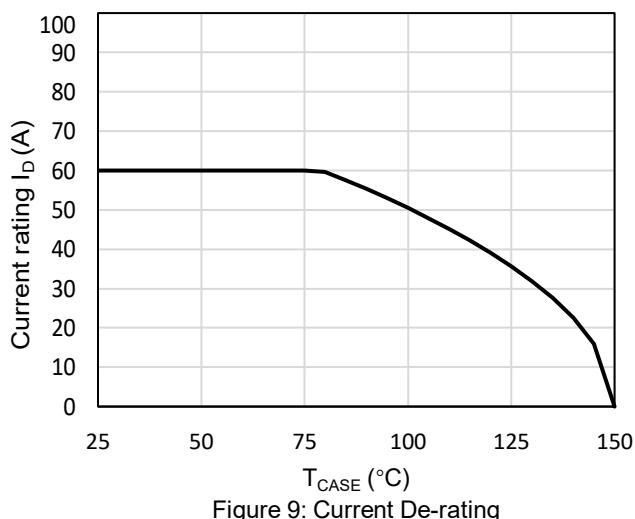


Figure 9: Current De-rating

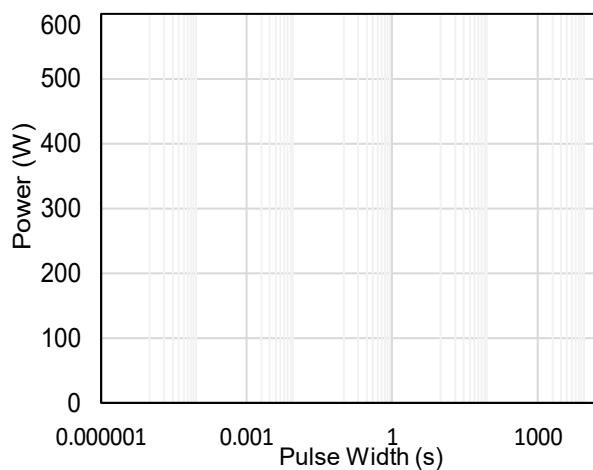


Figure 10: Single Pulse Power Rating Junction-to-Case

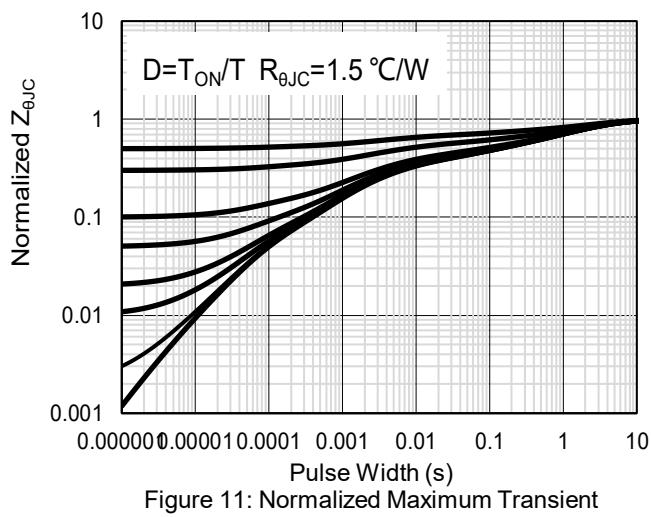


Figure 11: Normalized Maximum Transient Thermal Impedance

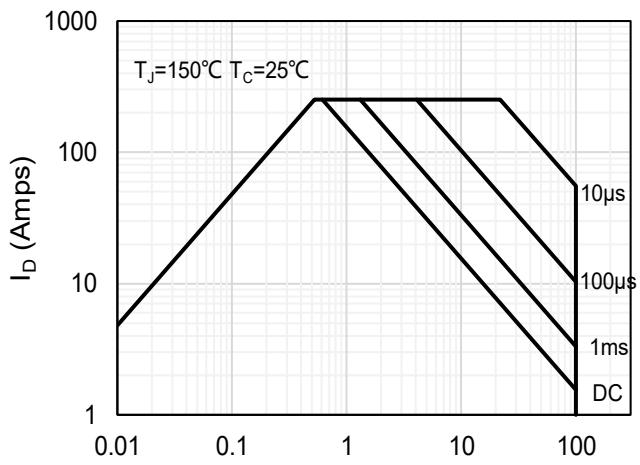
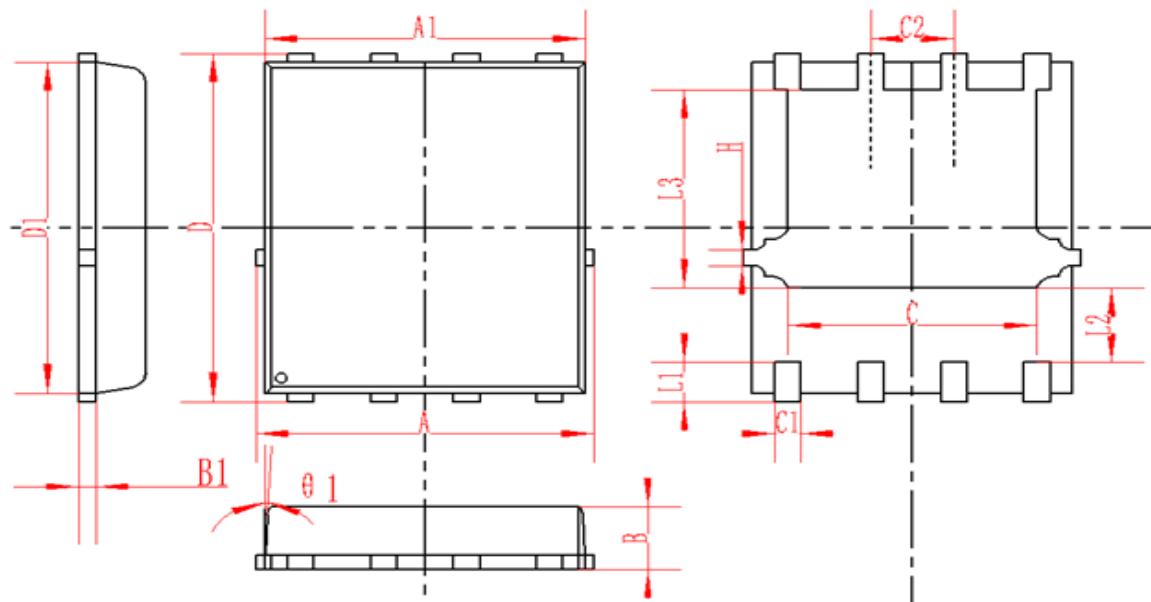


Figure 12: Maximum Forward Biased Safe Operating Area



DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010



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